

REMARKS

Claims 1-5 were pending in the above referenced application. Claim 2 is canceled without prejudice and Claims 1 and 3-5 are amended. Therefore, Claims 1, and 3-5 are currently pending.

Rejection under 35 U.S.C. §112

Claims 2-5 stand rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Without admission or concurrence with the Examiner's remarks regarding a "shift of focus," Applicant has amended Claims 2-5 in an effort to expedite the prosecution of the above-referenced application. Such amendments do not change the scope of what is claimed in any manner.

Therefore, Applicant respectfully asserts that Claims 2-5 are in condition for allowance, which action is earnestly sought.

Rejections under 35 USC 102


Claim 1 stands rejected under 35 U.S.C. 102(e) as being anticipated by each of Cohen et al. (US 5,800,626, hereinafter "Cohen"), Sakurai et al. (US 6,082,373, hereinafter "Sakurai") and Yeol et al. (US 6,039,815, hereinafter "Yeol"). Applicant traverses.

Claim 1 is amended to recite, among other things, "employing the liquid having the increased total dissolved gas concentration for a semiconductor polishing process." Each of Cohen, Sakurai and Yeol are directed to cleaning processes and do not teach or even suggest a polishing process. Since it is

a requirement that "for anticipation under U.S.C. 102, the reference must teach every aspect of the claimed invention either explicitly or impliedly" (M.P.E.P. 706.02). None of Cohen, Sakurai or Yeol meets this requirement. It necessarily follows then that the instant rejection should be withdrawn and Claim 1 allowed. Action to this effect is earnestly sought.

In summary, Applicant having responded to each of the rejections, respectfully asserts that Claims 1 and 3-5 are in condition for allowance. Action to that effect is earnestly sought. If, however the Examiner's next action is anything other than a Notice of Allowance, the Examiner is requested to call the undersigned to schedule a telephonic interview.

Respectfully submitted,

Dated: March 13, 2001 By: 
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/298,160
Filing Date April 22, 1999
Inventor Dan G. Custer et al.
Assignee Micron Technology, Inc.
Group Art Unit 1746
Examiner A. Olsen
Attorney's Docket No. MI22-1172
Title: Polishing Systems, Methods of Polishing Substrates, and Methods of
Preparing Liquids for Semiconductor Fabrication Processes

VERSION WITH MARKINGS TO SHOW CHANGES MADE
ACCOMPANYING RESPONSE TO December 15, 2000 OFFICE ACTION

The claims have been amended as follows. Underlines indicate
insertions and ~~strikeouts~~ indicate deletions.

1. (Amended) A method of preparing a liquid for a semiconductor
fabrication process comprising:

- providing a liquid;
- degassifying the liquid;

injecting a gas into the liquid to regassify the liquid, the
regassification increasing a total dissolved gas concentration in the liquid
to greater than or equal to 200 ppb, and

employing the liquid having the increased total dissolved gas
concentration for ~~the~~ a semiconductor polishing process.

Cancel Claim 2 without prejudice.

3. The method of claim 1 wherein the providing provides a water comprising liquid for the semiconductor ~~fabrication process is a~~ polishing process and the liquid ~~comprises water~~.

4. The method of claim 1 wherein the semiconductor polishing ~~fabrication process is~~ comprises an etch process.

5. The method of claim 1 wherein the semiconductor polishing ~~fabrication process is~~ comprises a wet etch process and the liquid comprises water.